



Understanding Specs to Better Simulate Solder-to-Board Performance

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The Johnstech logo, consisting of the word 'Johnstech' in a white, sans-serif font. The 'u' in 'Johnstech' is underlined. A registered trademark symbol (®) is positioned to the upper right of the 'h'. The logo is set against a dark red rectangular background with a thin white border.

Agenda

- **Changes in Contactor performance**
 - Inductance effects
 - Thermal or current carrying effects
 - Cres and repeatability
- **Importance of design margins**
- **Effects of device configurations**
- **Mechanical considerations**
- **Test methods**
- **Conclusion**



Causes of Changes in Performance

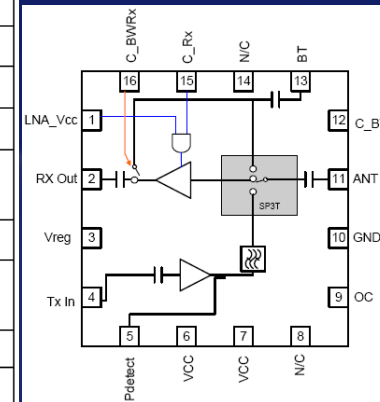
- **Variations in signal path**
- **Variations in insertion position**
- **Variations in oxides and debris buildup**
- **Variations in package platings**
- **Variations in I/O pitch**
- **Variations in location of ground or return path**
- **Variations in insertion forces and speed**

High Gain Amplifier Spec Sheet

| Parameter | Specification | | | Unit | Condition | | |
|-----------------------------------|---------------|------|------|------|---|---|---|
| | Min. | Typ. | Max. | | | | |
| 2.4GHz Transmit Parameters | | | | | Front End Module | | |
| Compliance | | | | | IEEE802.11b, IEEE802.11g, FCC CFG 15.247, .205, .209, EN, and JDEC | | |
| Nominal Conditions | | | | | Specifications must be met across V_{CC} , V_{REG} , and Temperature; unless otherwise specified. | | |
| Frequency | 2.4 | | 2.5 | GHz | | | |
| Power Supply | 3.0 | 3.3 | 4.2 | V | PA nominal voltage supply (V_{CC}) | | |
| V_{REG} Voltage | | | | | | | |
| | ON | 3.0 | 3.1 | 3.2 | V | PA in "ON" state | |
| | OFF | | 0.00 | 0.20 | V | PA in "OFF" state | |
| Output Power | | | | | | | |
| | 11g | 18 | 18.5 | | dBm | 54Mbps, OFDM 54Mbps, $V_{CC} \geq 3.0V$ | |
| | | | 19 | 19.5 | | dBm | 54Mbps, OFDM 54Mbps, $V_{CC} \geq 3.3V$ |
| | 11b | 20 | 22 | | dBm | 11Mbps, CCK, $V_{CC} \geq 3.0V$ | |
| EVM | | | 3.3 | 4.0 | % | $P_{OUT(g)}$ = Rated Output Power, 54Mbps OFDM, 50Ω, see note 1 | |
| Adjacent Channel Power | | | | | | $P_{OUT(b)}$ = 20dBm 1Mbps CCK, note 2 | |
| | ACP1 | | -36 | -33 | dBc | $V_{CC} \geq 3.3V$, meeting 11b spectral mask requirements | |
| | ACP2 | | -56 | -51 | dBc | | |
| Gain | | 26 | 30 | 34 | dB | | |
| Gain Variation Slope | | | | | | At rated power and a given supply voltage, room temp | |
| | Range | 3.0 | | 4.2 | V | | |
| | Frequency | -0.5 | | +0.5 | dB | 2.4GHz to 2.5GHz | |

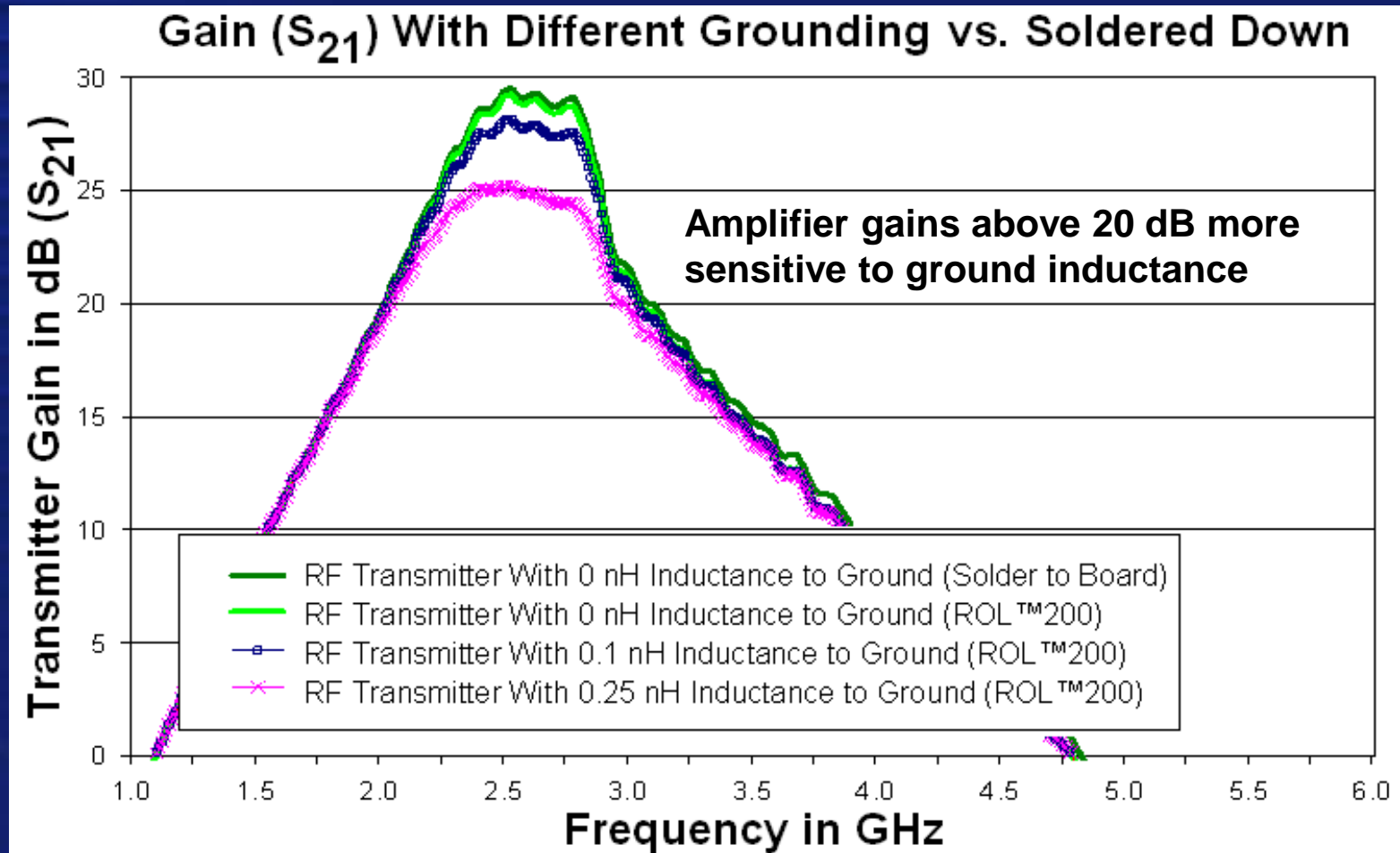
<http://www.rfmd.com/CS/Documents/RF5755D5.pdf>

Schematic



Testing at hot will stress device if die temperature is exceeded!

Effects of Inductance



Higher amplifier gains require lower ground inductance!!

High Power Amplifier Spec Sheet

| Parameter | Specification | | | Unit | Condition |
|--|---------------|------|------|------|--|
| | Min. | Typ. | Max. | | |
| Typical Conditions | | | | | Temp = 25 °C, Frequency = 2.3GHz to 3.8GHz depending on the evaluation board tune, V _{CC} = V _{PC} = 6.0V unless otherwise specified |
| Frequency | 2.3 | | 2.5 | GHz | Tune A |
| | 2.5 | | 2.7 | GHz | Tune B |
| | 2.7 | | 2.9 | GHz | Tune C |
| | 3.3 | | 3.8 | GHz | Tune D |
| Output Power | | 30 | | | Tune A, B, C, D |
| EVM | | 3.0 | | % | 802.16e 16QAM 3/4 modulation, P _{OUT} = +30 dBm |
| Stability | 0 | | 33 | dBm | PA should be stable when P _{OUT} is measured from 0dBm to 33dBm |
| Gain | | 11 | | dB | |
| Gain Flatness | | | 3 | dB | Peak-Peak over any 300MHz bandwidth |
| Noise Figure | | 5 | | dB | |
| Operating Current | | 1.3 | | Amp | RF P _{OUT} = +30 dBm, V _{CC} = 6V |
| Quiescent Current | | 900 | | mA | |
| I _{VPC} Current | | 10 | | mA | No RF |
| Leakage Current | | 100 | | uA | |
| Turn-on Time from Setting of V _{BIAS} | | | 400 | ns | Output stable within 90% of final gain |
| Input Return Loss | | -15 | -10 | dB | In tune band |
| Output Return Loss | | -10 | -7 | dB | In tune band |
| Stable into Output VSWR | | | 4:1 | | No spurs above -47 dBm |

<http://www.rfmd.com/CS/Documents/RF5643D5.pdf>

Amplifiers have large bandwidths so it is difficult to optimize performance! Large DC power, 1W RF out -> rest is heat!!

Material Softening/Melting Voltages

| <u>Material</u> | <u>Softening Volts (V)</u> | <u>Melting Volts (V)</u> |
|-----------------|----------------------------|--------------------------|
| Aluminum | 0.10 | 0.30 |
| Iron | 0.19 | 0.19 |
| Nickel | 0.16 | 0.16 |
| Copper | 0.12 | 0.43 |
| Zinc | 0.10 | 0.17 |
| Silver | 0.09 | 0.37 |
| Cadmium | 0.15 | 0.16 |
| Tin | 0.07 | 0.13 |
| Gold | 0.08 | 0.43 |
| Palladium | 0.57 | 0.57 |
| Lead | 0.12 | 0.19 |
| 60Cu,40Zn | 0.20 | 0.25 |

Source: Timron Scientific Inc., *Electrical Contacts And Electroplates In Separable Connectors*

The low melting voltage of Matte Tin can cause test problems!!

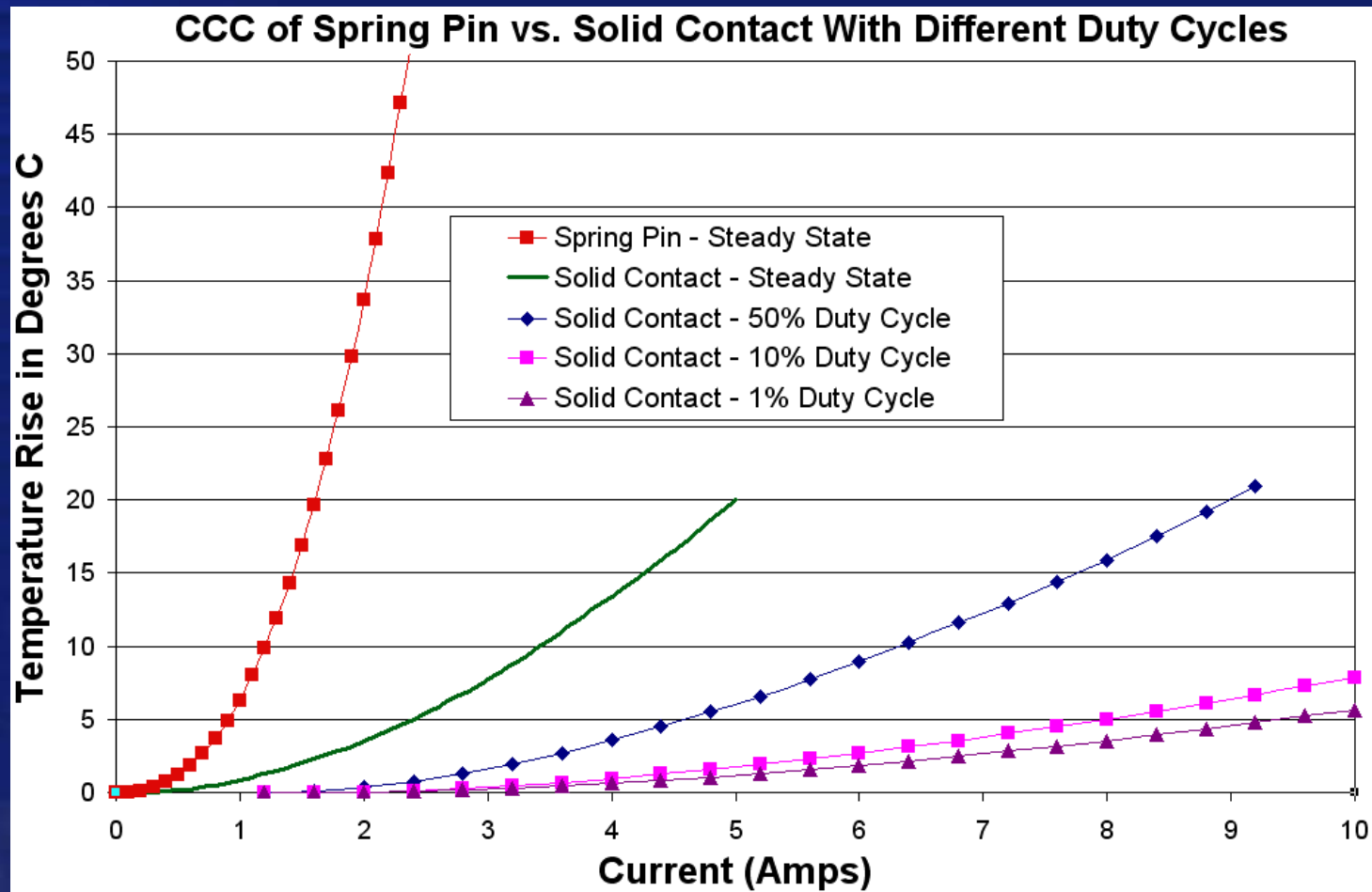
Current Carrying Example Calculations

For Matte Tin Plated Device

| Contact Resistance | Current to Soften | Current to Melt |
|--------------------|-------------------|-----------------|
| 20 mOhms | 3.5 A | 6.5A |
| 50 mOhms | 1.4 A | 2.6 A |
| 100 mOhms | 0.7 A | 1.3 A |
| 150 mOhms | 0.47 A | 0.87 A |
| 200 mOhms | 0.35 A | 0.65 A |
| 250 mOhms | 0.28 A | 0.52 A |
| 500 mOhms | 140 mA | 260 mA |

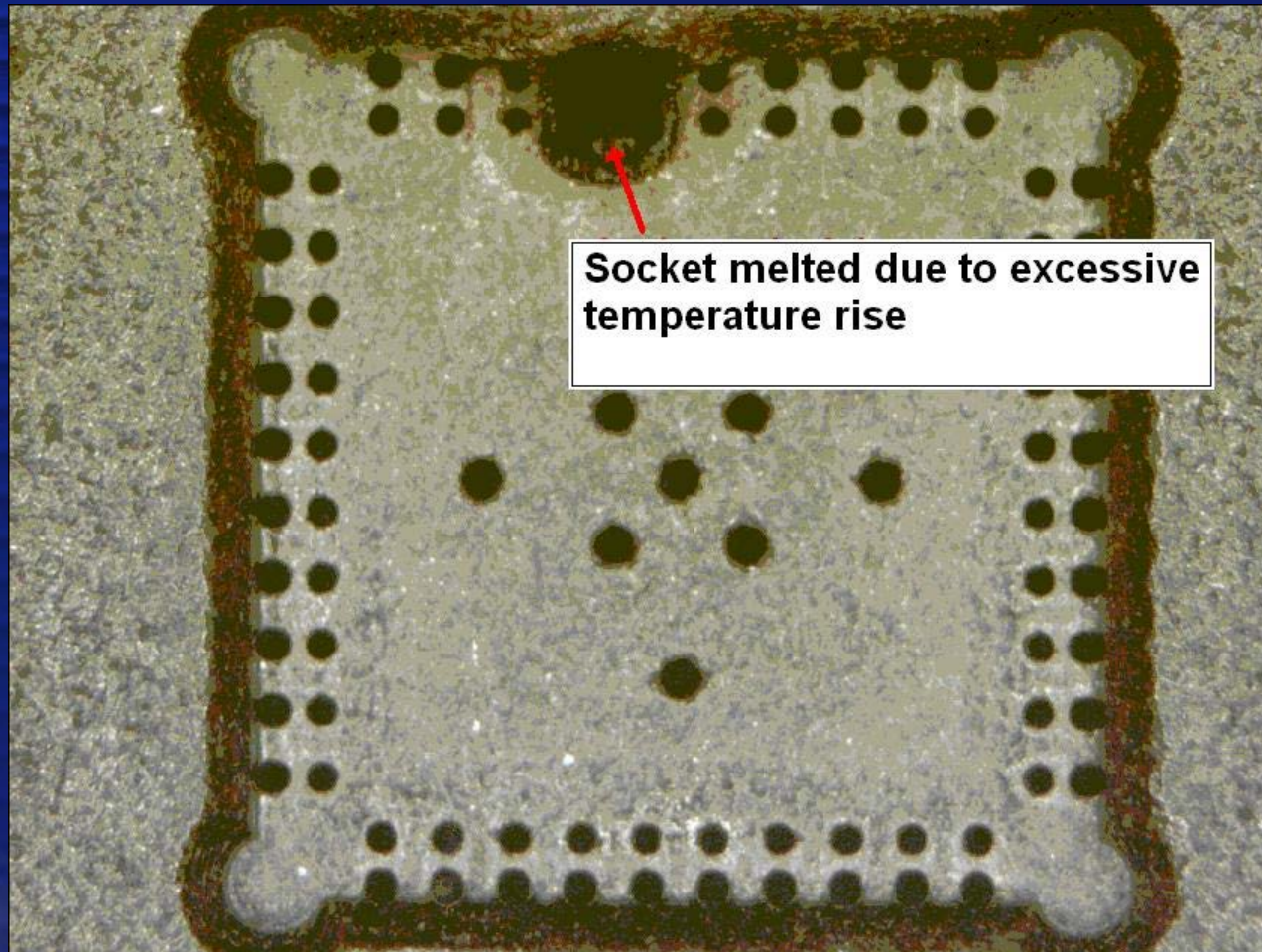
Lower C_{res} solutions enable higher current carrying capability!!

0.5mm Pitch Socket Contacts Current Carrying Capacity



Test times can be longer with less current carrying capability!!

Socket With Too Much C_{res}



Customer later switched to Contactor using solid contacts to dissipate heat required to achieve desired test times.

Oops!! Excessive heat caused by normal increases in C_{res} and not considering required production duty cycles can melt sockets!!

RDSon Measurements Needs Low C_{res}

FEATURES

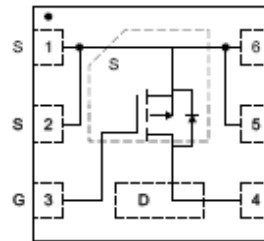
- SON 2-mm × 2-mm Plastic Package **Top View**

APPLICATIONS

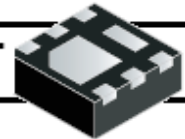
- Battery Management
- Load Management
- Battery Protection

DESCRIPTION

The device has been designed to deliver the lowest on resistance and gate charge in the smallest outline possible with excellent thermal characteristics in an ultra low profile for space constrained applications.



P-Channel NexFET™ Power MOSFET



PRODUCT SUMMARY

| | | | |
|---------------------|-------------------------------|-------------------------|-------|
| V _{DS} | Drain to Source Voltage | -20 | V |
| Q _g | Gate Charge Total (-4.5V) | 2.6 | nC |
| Q _{gd} | Gate Charge Gate to Drain | 0.5 | nC |
| R _{DS(on)} | Drain to Source On Resistance | V _{GS} = -1.8V | 71 mΩ |
| | | V _{GS} = -2.5V | 56 mΩ |
| | | V _{GS} = -4.5V | 39 mΩ |
| V _{GS(th)} | Threshold Voltage | -0.65 | V |

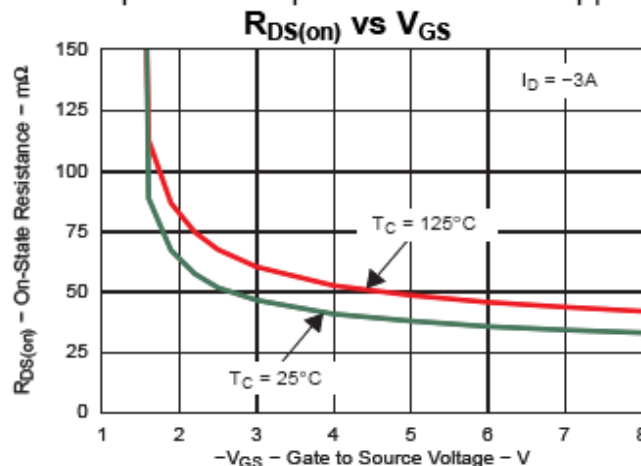
ABSOLUTE MAXIMUM RATINGS

| T _A = 25°C unless otherwise stated | | VALUE | UNIT |
|---|--|------------|------|
| V _{DS} | Drain to Source Voltage | -20 | V |
| V _{GS} | Gate to Source Voltage | ±8 | V |
| I _D | Continuous Drain Current, T _C = 25°C | -5 | A |
| | Continuous Drain Current ⁽¹⁾ | -5 | A |
| I _{DM} | Pulsed Drain Current, T _A = 25°C ⁽²⁾ | -20 | A |
| P _D | Power Dissipation | 2.4 | W |
| T _J , T _{STG} | Operating Junction and Storage Temperature Range | -55 to 150 | °C |

(1) Package Limited

(2) Pulse duration 10 μs, duty cycle ≤2%

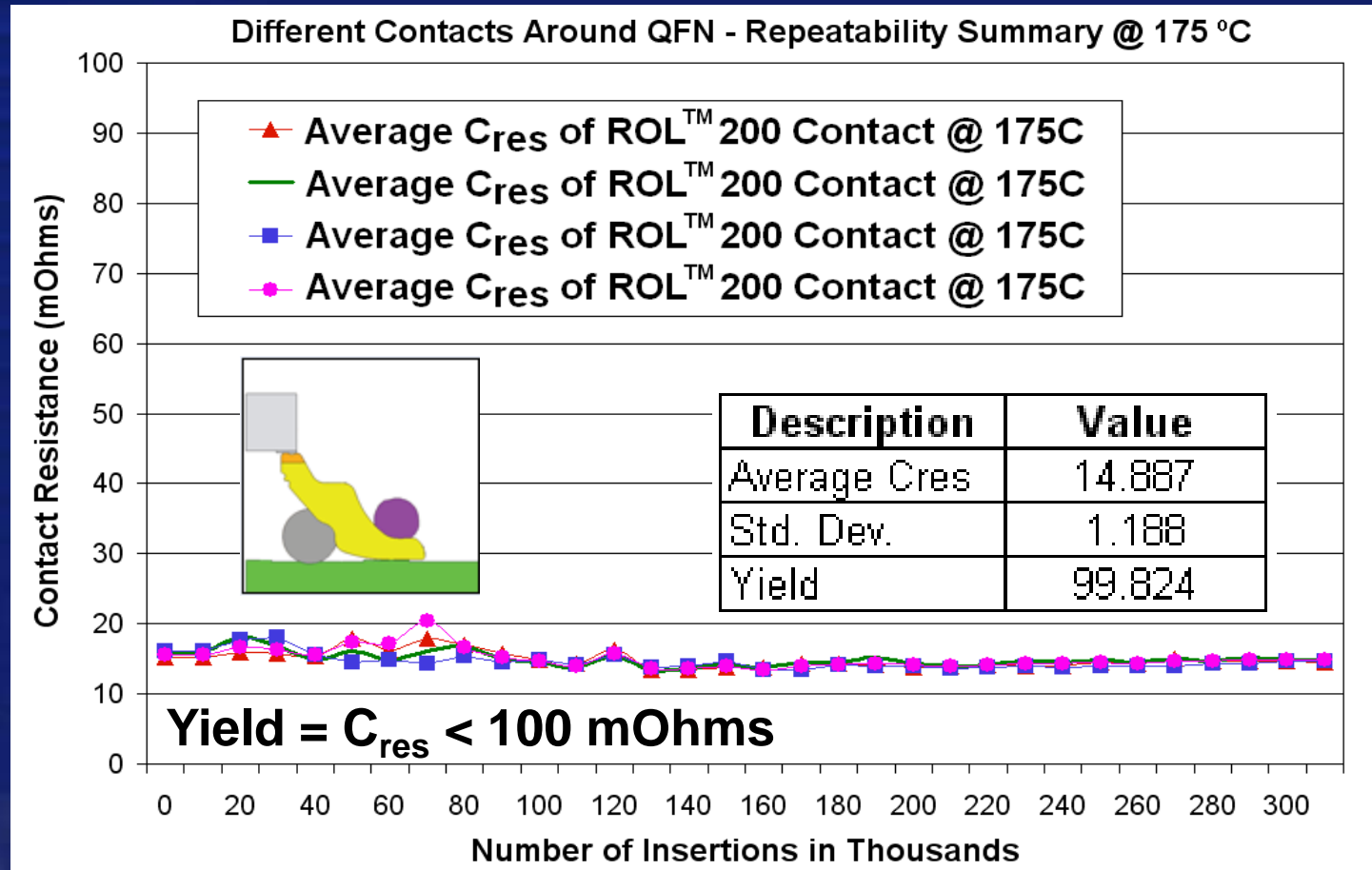
<http://www.ti.com/lit/ds/symlink/csd25302q2.pdf>



Wide variations in Contact C_{res} cause excessive false failures!!

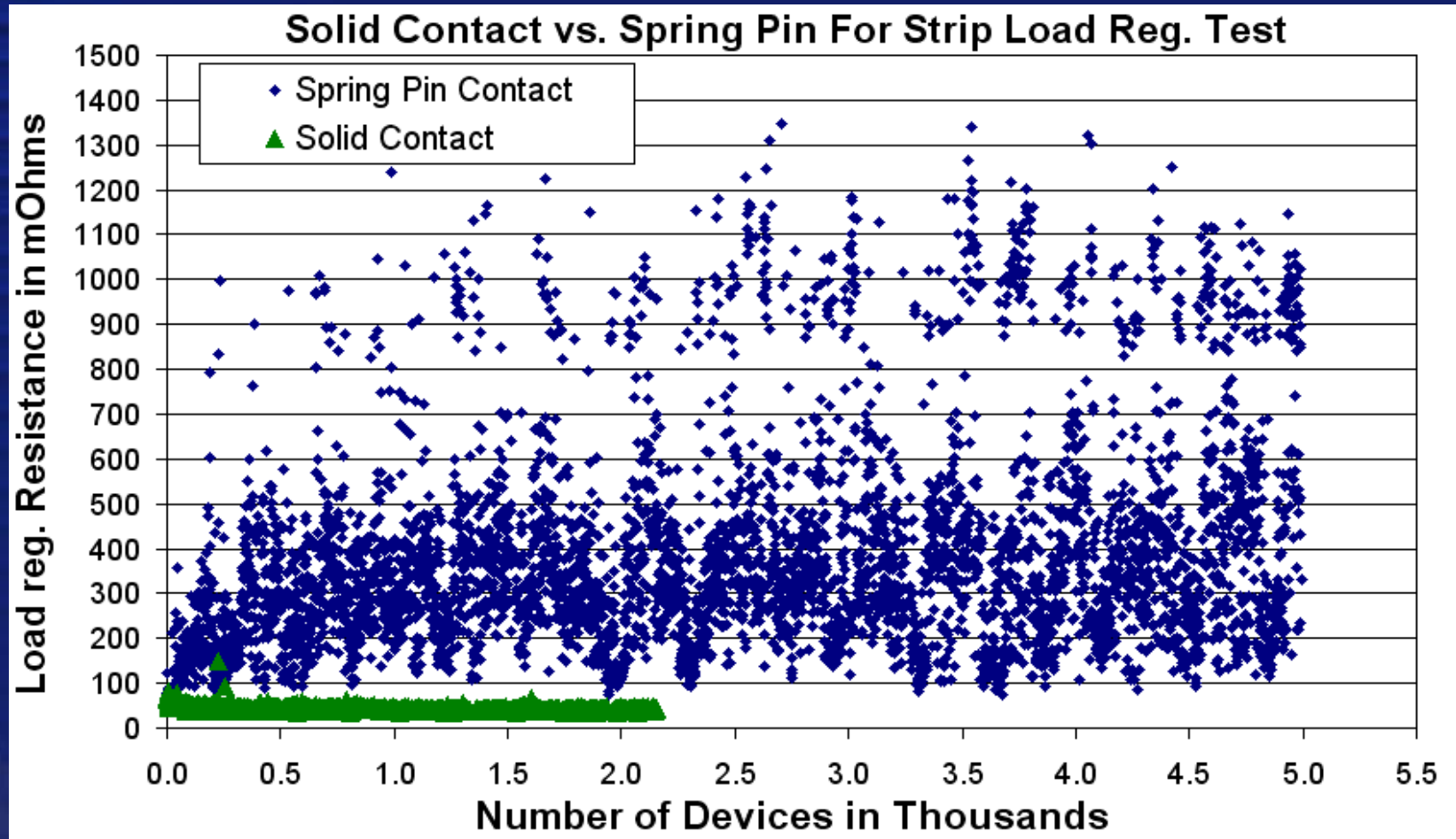
ROL™ Technology C_{res}

With NiPdAu Plated Device @ 175 °C



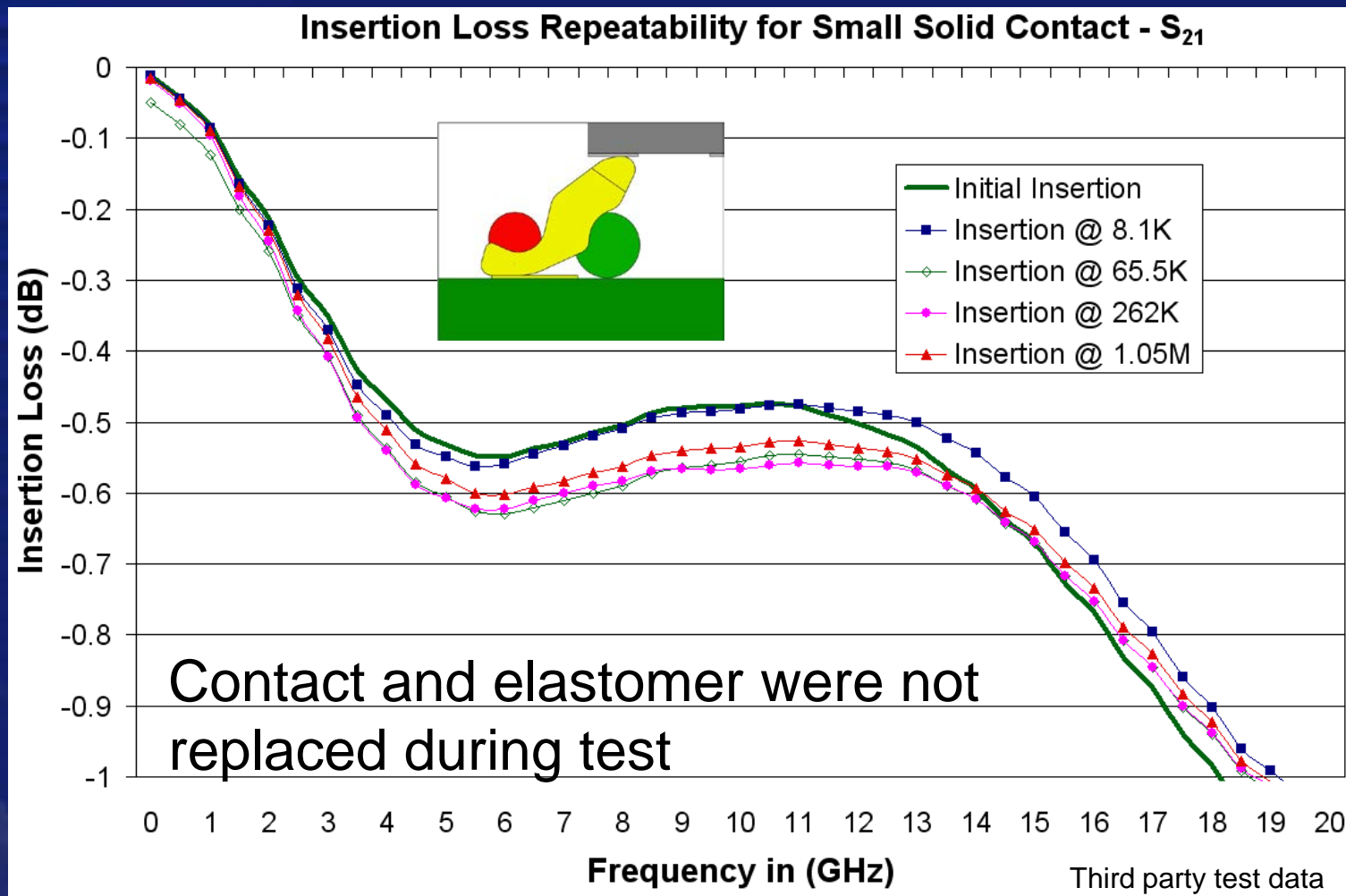
Solid contacts provide low and stable C_{res} !

Contact Resistance Repeatability – Solid Contact vs. Spring Pin



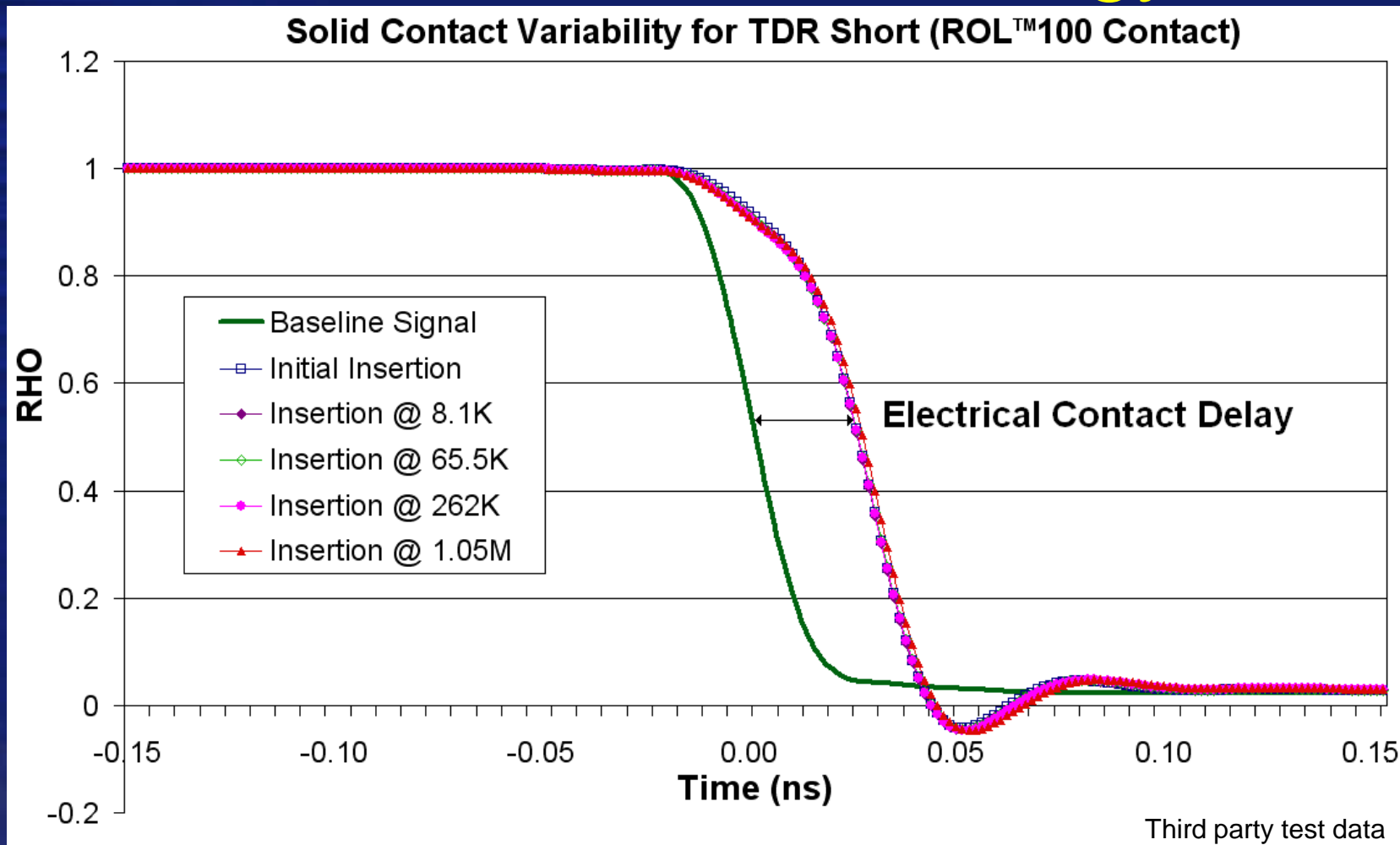
Actual production data shows C_{res} variability causing false failures!

Contact RF Repeatability – Solid ROL™ Technology



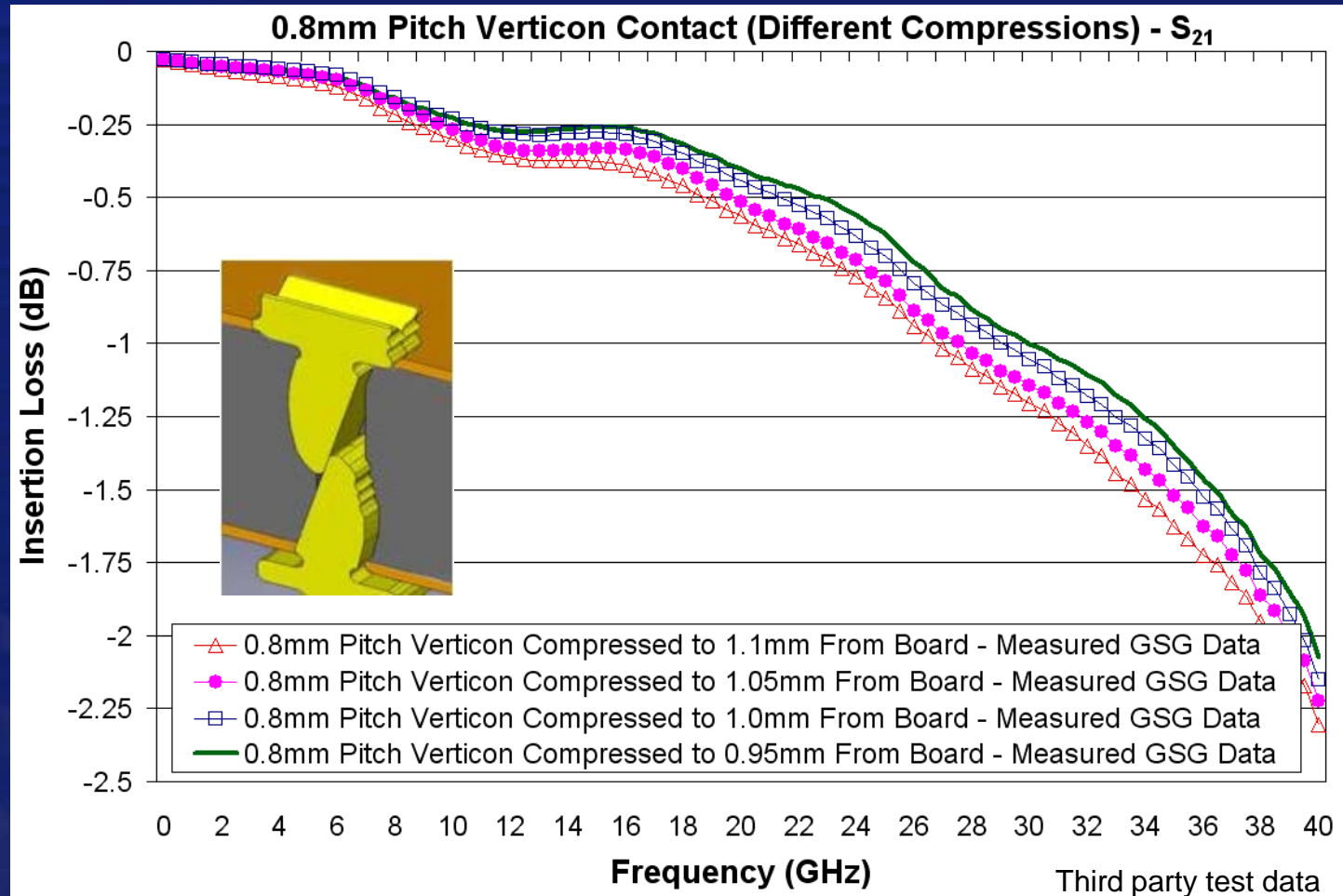
Solid contact has very good RF repeatability!

Contactors Digital Repeatability – Solid ROL™ Technology



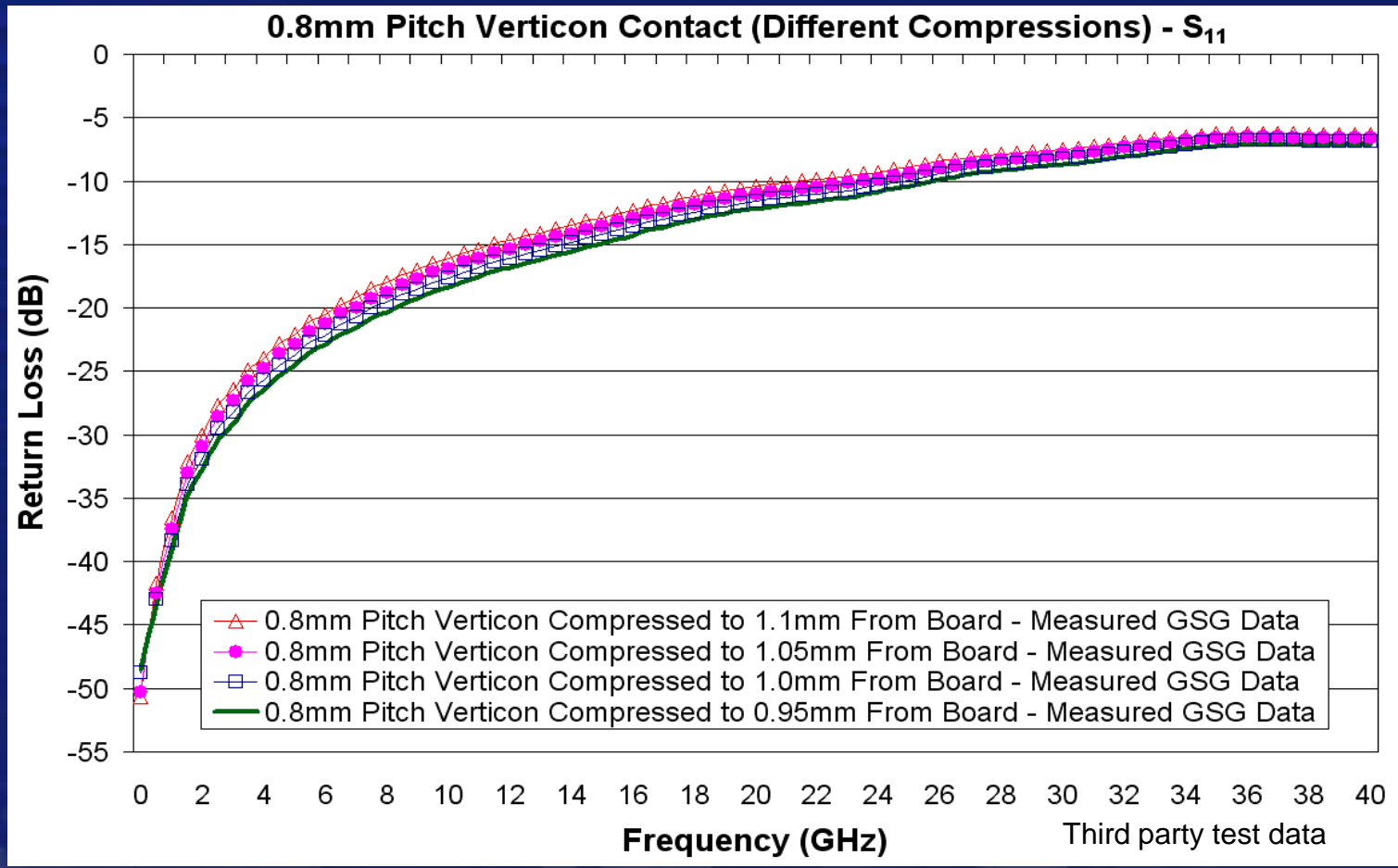
Solid contact has consistent repeatable delay!

0.8mm Pitch Verticon[®] 100 BGA Insertion Loss vs. Compression – S_{21}



Shorter Contact lengths improve RF performance!

0.8mm Pitch Verticon[®] 100 BGA Return Loss vs. Compression – S_{11}



Increasing contact interfaces increases variation in RF performance during compression!

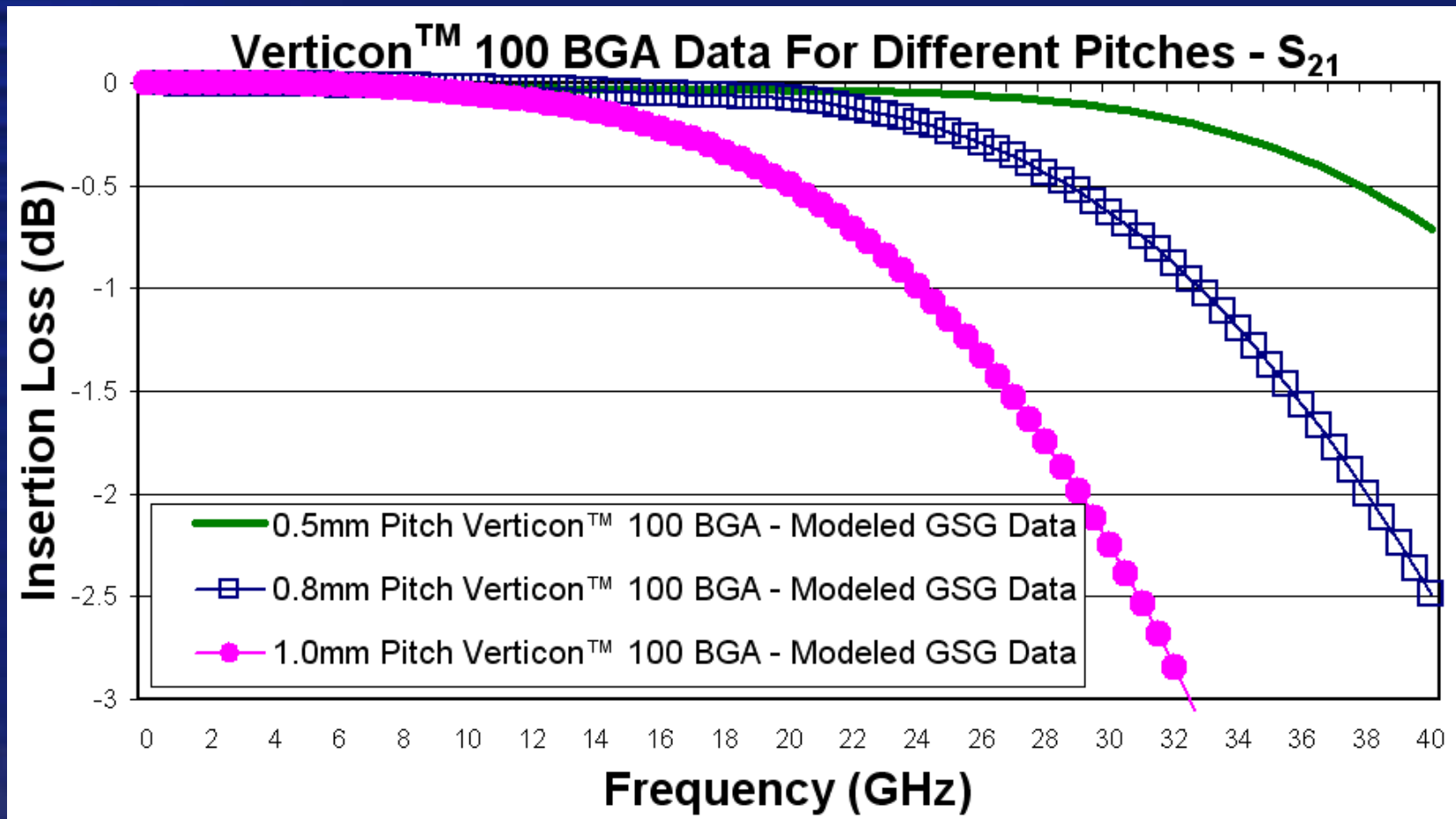
Importance of Design Margin

- Contact resistance will increase over time
- Debris or oxides may impact C_{res} or ground inductance path
- IR drop across interfaces could cause softening or melting of device plating
- Variation in signal path and ground location will vary electrical performance

All of these will affect Guard Bands and Test Limits

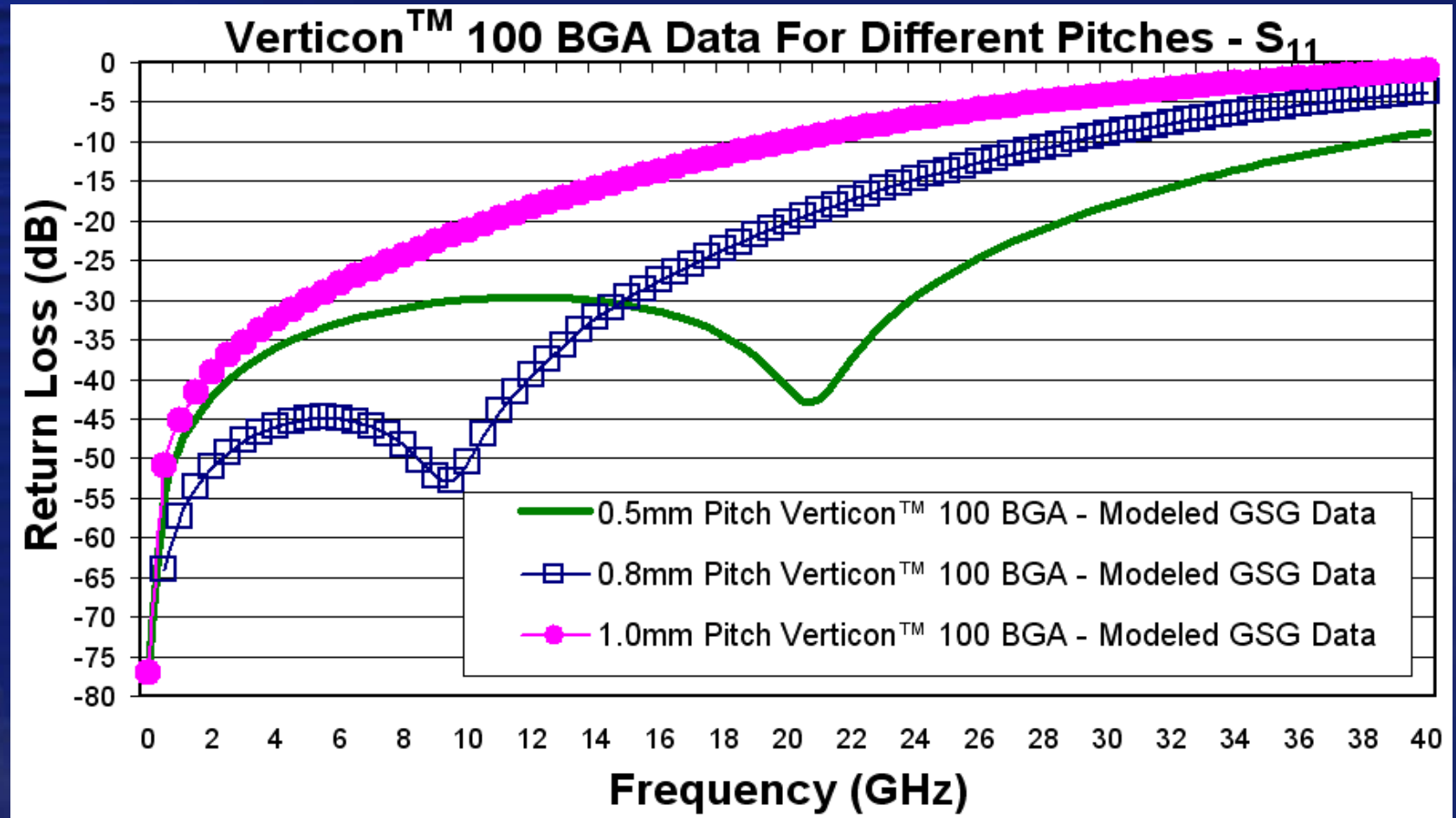
NOTE: The contactor will always add more ground inductance and resistance to the path than solder-to-board performance!

Verticon[®] 100 BGA Modeled Data For Different Pitches – S_{21}



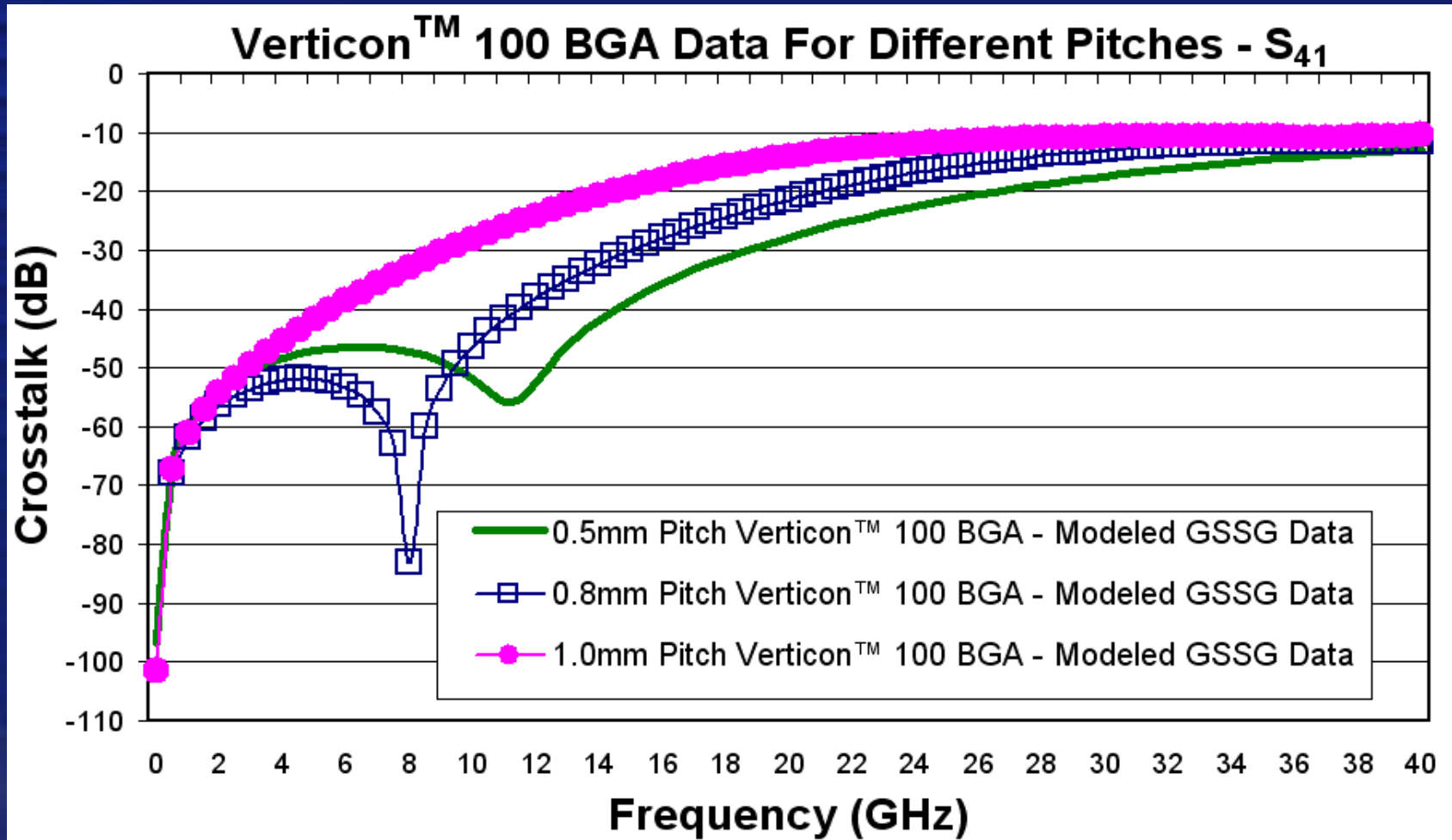
Proximity of grounds affects performance at higher frequencies!

Verticon[®] 100 BGA Modeled Data For Different Pitches – S_{11}



Both pitch and contact design impacts characteristic impedance!

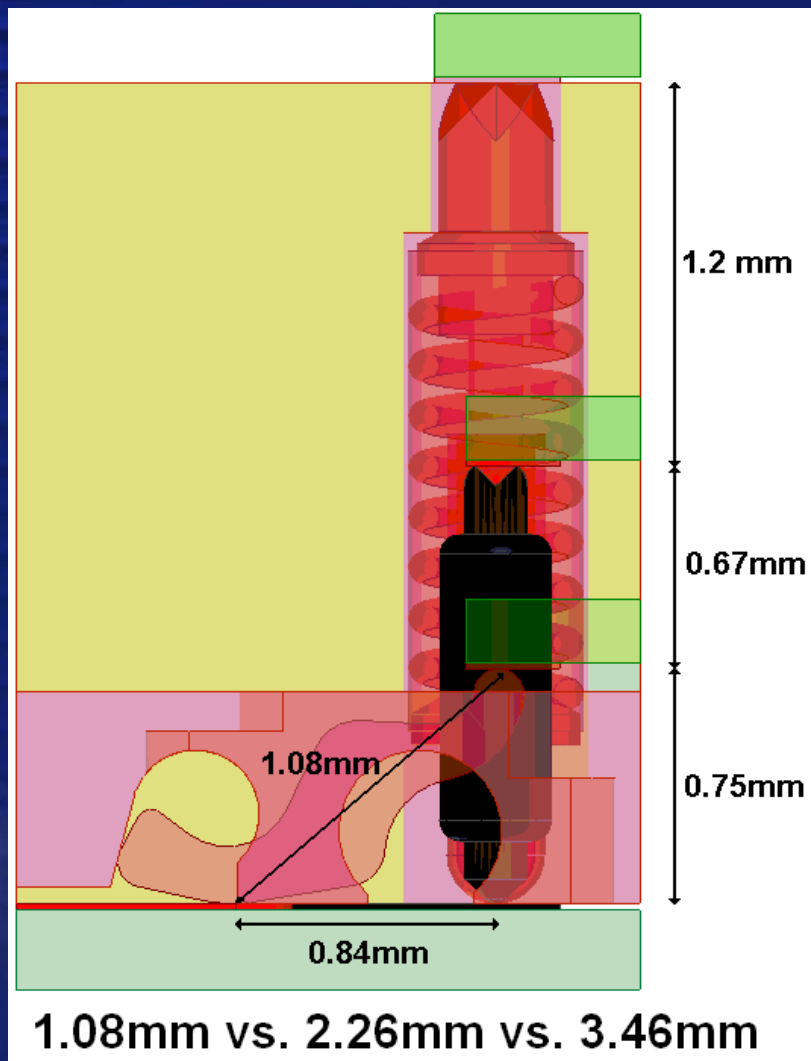
Verticon[®] 100 BGA Modeled Data For Different Pitches – S₄₁



Return loss is correlated to Crosstalk!

Signal Transition Comparison

RF Signal Launch vs. Airplane Take Off



RF performance degrades with every right angle connection!!

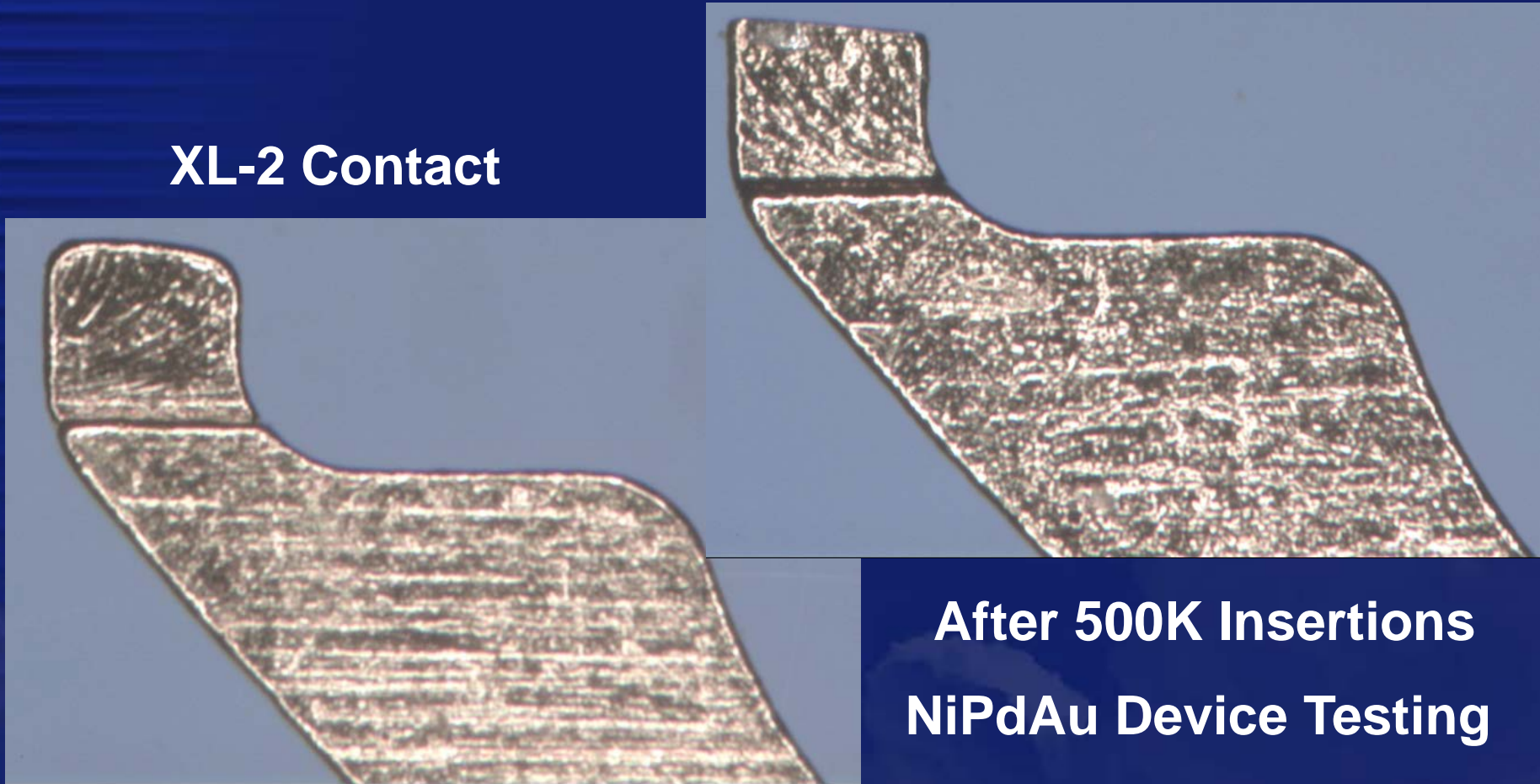
Mechanical Considerations

- Wiping action vs. no wiping action effects MTBA and cleaning intervals
- One piece vs. multiple parts : more parts = more variability
- Handler interface issues – insertion speed
- Maintenance of parts
- Test conditions affect performance

Mechanical features also affect RF performance!

Solid Contact Shows Minimal Wear After 500K Insertions

XL-2 Contact



**After 500K Insertions
NiPdAu Device Testing**

C_{res} Test Method Differences

- Testing with correct device plating
 - Gold on gold gives best results. Majority of packages use other platings (i.e. Matte Tin and NiPdAu)
 - Hardness of plating affects performance
 - Oxide level affects performance
 - Wear and contaminants affect life
 - Wiping or self cleaning action affect MTBA
- Testing at correct forces and insertion speeds
 - Higher the force the lower the C_{res}
 - Higher the force the shorter the contact life and MTBA

Conclusion

- Ground inductance is extremely important when measuring high frequency signals and devices with high gain
- Shorter paths result in better electrical performance (hypotenuse shorter than sum of legs)
- Solid contacts have current carrying advantages over contacts with multiple parts
- Fewer contact interfaces result in lower C_{res}
- Repeatability improves both electrical and mechanical data accuracy resulting in higher yields
- Not all specifications are created equal